

# 2N6519BU Datasheet

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DiGi Electronics Part Number	2N6519BU-DG
Manufacturer	<a href="#">onsemi</a>
Manufacturer Product Number	2N6519BU
Description	TRANS PNP 300V 0.5A TO92-3
Detailed Description	Bipolar (BJT) Transistor PNP 300 V 500 mA 200MHz 625 mW Through Hole TO-92-3



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

2N6519BU

Series:

-

Transistor Type:

PNP

Voltage - Collector Emitter Breakdown (Max):

300 V

Current - Collector Cutoff (Max):

50nA (ICBO)

Power - Max:

625 mW

Operating Temperature:

-55°C ~ 150°C (TJ)

Package / Case:

TO-226-3, TO-92-3 (TO-226AA)

Base Product Number:

2N6519

Manufacturer:

onsemi

Product Status:

Obsolete

Current - Collector (Ic) (Max):

500 mA

Vce Saturation (Max) @ Ib, Ic:

1V @ 5mA, 50mA

DC Current Gain (hFE) (Min) @ Ic, Vce:

40 @ 50mA, 10V

Frequency - Transition:

200MHz

Mounting Type:

Through Hole

Supplier Device Package:

TO-92-3

## Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

REACH Unaffected

HTSUS:

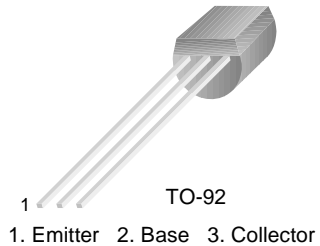
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## 2N6519

### High Voltage Transistor

- Collector-Emitter Voltage:  $V_{CE0} = -300V$
- Collector Dissipation:  $P_C (\text{max}) = 625mW$



### PNP Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-300	V
$V_{CEO}$	Collector-Emitter Voltage	-300	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-500	mA
$I_B$	Base Current	-250	mA
$P_C$	Collector Power Dissipation	625	W
	Derate above $25^\circ\text{C}$	5	mW/ $^\circ\text{C}$
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-55 ~ 150	$^\circ\text{C}$

• Refer to 2N6520 for graphs

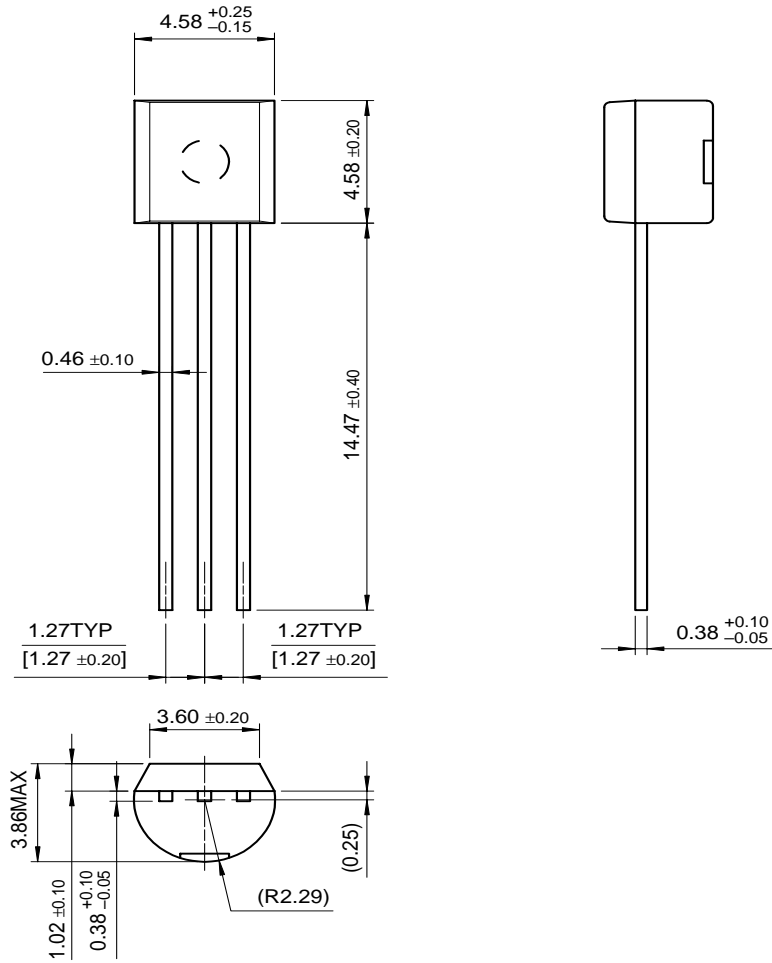
#### Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = -100\mu\text{A}, I_E = 0$	-300		V
$BV_{CEO}$	* Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}, I_B = 0$	-300		V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}, I_C = 0$	-5		V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = -200V, I_E = 0$		-50	nA
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = -4V, I_C = 0$		-50	nA
$h_{FE}$	* DC Current Gain	$V_{CE} = -10V, I_C = -1\text{mA}$	30		
		$V_{CE} = -10V, I_C = -10\text{mA}$	45		
		$V_{CE} = -10V, I_C = -30\text{mA}$	45	270	
		$V_{CE} = -10V, I_C = -50\text{mA}$	40	200	
		$V_{CE} = -10V, I_C = -100\text{mA}$	20		
$V_{CE} (\text{sat})$	Collector-Emitter Saturation Voltage	$I_C = -10\text{mA}, I_B = -1\text{mA}$		-0.30	V
		$I_C = -20\text{mA}, I_B = -2\text{mA}$		-0.35	V
		$I_C = -30\text{mA}, I_B = -3\text{mA}$		-0.50	V
		$I_C = -50\text{mA}, I_B = -5\text{mA}$		-1	V
$V_{BE} (\text{sat})$	Base-Emitter Saturation Voltage	$I_C = -10\text{mA}, I_B = -1\text{mA}$		-0.75	V
		$I_C = -20\text{mA}, I_B = -2\text{mA}$		-0.85	V
		$I_C = -30\text{mA}, I_B = -3\text{mA}$		-0.90	V
$V_{BE} (\text{on})$	Base-Emitter On Voltage	$V_{CE} = -10V, I_C = -100\text{mA}$		-2	V
$f_T$	* Current Gain Bandwidth Product	$V_{CE} = -20V, I_C = -10\text{mA}, f = 20\text{MHz}$	40	200	MHz
$C_{ob}$	Output Capacitance	$V_{CB} = -20V, I_E = 0, f = 1\text{MHz}$		6	pF
$C_{EB}$	Emitter-Base Capacitance	$V_{EB} = -0.5V, I_C = 0, f = 1\text{MHz}$		100	pF
$t_{ON}$	Turn On Time	$V_{BE} (\text{off}) = -2V, V_{CC} = -100V$ $I_C = -50\text{mA}, I_{B1} = -10\text{mA}$		200	ns
$t_{OFF}$	Turn Off Time	$V_{CC} = -100V, I_C = -50\text{mA}$ $I_{B1} = I_{B2} = 10\text{mA}$		3.5	ns

\* Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

# Package Dimensions

## TO-92



Dimensions in Millimeters

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